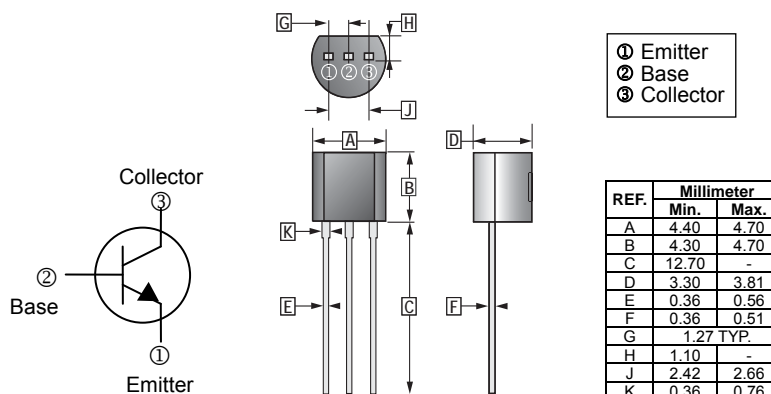


RoHS Compliant Product
A suffix of "-C" specifies halogen & lead-free

FEATURES

- General Purpose Amplifier Transistor

TO-92



ABSOLUTE MAXIMUM RATINGS (T_A = 25°C unless otherwise specified)

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V _{CB0}	40	V
Collector to Emitter Voltage	V _{CEO}	40	V
Emitter to Base Voltage	V _{EBO}	3	V
Collector Current - Continuous	I _C	0.1	A
Collector Power Dissipation	P _C	300	mW
Thermal resistance, junction to ambient	R _{θJA}	416	°C / W
Junction, Storage Temperature	T _J , T _{STG}	150, -55~150	°C

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise specified)

Parameter	Symbol	Min	Typ	Max	Unit	Test Condition
Collector to Base Breakdown Voltage	V _{(BR)CBO}	40	-	-	V	I _C = 0.01mA, I _E = 0A
Collector to Emitter Breakdown Voltage	V _{(BR)CEO}	40	-	-	V	I _C = 1mA, I _B = 0A
Emitter to Base Breakdown Voltage	V _{(BR)EBO}	3	-	-	V	I _E = 0.01mA, I _C = 0A
Collector Cut-Off Current	I _{CBO}	-	-	0.1	μA	V _{CB} = 60V, I _E = 0A
Collector Cut-Off Current	I _{CEX}	-	-	50	nA	V _{CE} = 30V, V _{BE(off)} = 3V
Emitter Cut-Off Current	I _{EBO}	-	-	0.1	μA	V _{EB} = 5V, I _C = 0 mA
DC Current Gain	h _{FE}	30	-	200		V _{CE} = 1V, I _C = 12mA
Collector to Emitter Saturation Voltage	V _{CE(sat)}	-	-	0.3	V	I _C = 50mA, I _B = 5mA
Base to Emitter Saturation Voltage	V _{BE(sat)}	-	-	0.95	V	I _C = 50mA, I _B = 5mA
Transition Frequency	f _T	360	-	-	MHz	V _{CE} = 20V, I _C = 10mA, f = 100MHz